

	Type	L #	Hits	Search Text	DBs	Time Stamp	Com ments	Er ro rs
1	BRS	L2	17	WU-CHIH-NING.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/20 11:12		0
2	BRS	L3	8384	((wash\$3 or clean\$3 or etch\$3 or rins\$3) same (cupric oxide or "CuO" or "copper (II) oxide" or "copper oxide") same (HF or hydrfluoric or "NH.sub.2OH" or "NH.sub.4 F" or "ammonium fluoride")) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/20 11:20		0
3	BRS	L4	8384	((wash\$3 or clean\$3 or etch\$3 or rins\$3) same (cupric oxide or "CuO" or "copper (II) oxide") same (HF or hydrfluoric or "NH.sub.2OH" or "NH.sub.4 F" or "ammonium fluoride")) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/20 11:20		0
4	BRS	L5	5214	((wash\$3 or clean\$3 or etch\$3 or rins\$3) with (cupric oxide or "CuO" or "copper (II) oxide") with (HF or hydrfluoric or "NH.sub.2OH" or "NH.sub.4 F" or "ammonium fluoride")) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/20 11:22		0
5	BRS	L6	3240	5 and 438/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/20 11:21		0
6	BRS	L7	1926	6 and @pd<=20010716	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/20 11:23		0
7	BRS	L8	51	((wash\$3 or clean\$3 or etch\$3 or rins\$3) with (cupric oxide or "CuO" or "copper (II) oxide") with (HF or hydrfluoric or "NH.sub.2OH" or "NH.sub.4 F" or "ammonium fluoride")) same "pH") and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/20 11:23		0
8	BRS	L9	33	8 and @pd<=20010716	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/20 11:24		0

	Type	L #	Hits	Search Text	DBs	Time Stamp	Com men ts	Er ro r D ef in iti on	Er ro rs
9	BRS	L10	21	((wash\$3 or clean\$3 or etch\$3 or rins\$3) with (cupric oxide or "CuO" or "copper (II) oxide") with (HF or hydrfluoric or "NH.sub.2OH" or "NH.sub.4 F" or "ammonium fluoride"))) with "pH") and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/20 11:26			0
10	BRS	L11	15	10 and @pd<=20010716	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/20 11:24			0
11	BRS	L12	0	((wash\$3 or clean\$3 or etch\$3 or rins\$3) with ("cupric oxide" or "CuO" or "copper (II) oxide") with (HF or hydrfluoric or "NH.sub.2OH" or "NH.sub.4 F" or "ammonium fluoride"))) with "pH") and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/20 11:27			0
12	BRS	L13	0	((wash\$3 or clean\$3 or etch\$3 or rins\$3) same ("cupric oxide" or "CuO" or "copper (II) oxide") same (HF or hydrfluoric or "NH.sub.2OH" or "NH.sub.4 F" or "ammonium fluoride"))) same "pH") and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/20 11:27			0
13	BRS	L14	9	((wash\$3 or clean\$3 or etch\$3 or rins\$3) same ("cupric oxide" or "CuO" or "copper (II) oxide") same (HF or hydrfluoric or "NH.sub.2OH" or "NH.sub.4 F" or "ammonium fluoride"))) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/20 11:28			0